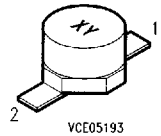
SIEMENS

Silicon Schottky Diodes

BAT 15- ... 5 S

- Beam lead technology
- Low dimension
- High performance
- Low barrier



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration	Package[1]
BAT 15-025 S	52	Q62702-A802		Cerec-X
BAT 15-055 S	55	Q62702-A805		
BAT 15-095 S	59	Q62702-A808		
BAT 15-115 S	51	Q62702-A810		

Maximum Ratings

Parameter	Symbol	Values		Unit
		BAT 15-025 S BAT 15-055 S	BAT 15-095 S BAT 15-115 S	
Reverse voltage	V_R	4	4	V
Forward current	I_F	100	50	mA
Junction temperature	T_j	175		°C
Storage temperature range	T_{stg}	– 55 ... + 150		
Operating temperature range	T_{op}	– 55 ... + 150		

[1] For detailed information see chapter Package Outlines.

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Electrical Characteristics
at T_A = 25 °C, unless otherwise specified.

Parameter		Symbol	Values			Unit
			min.	typ.	max.	
Breakdown voltage I_R = 10 µA		$V_{(BR)}$	4	–	–	V
Diode capacitance V_R = 0, f = 1 MHz		C_T				pF
	BAT 15-025 S		–	0.36	0.41	
	BAT 15-055 S		–	0.26	0.31	
	BAT 15-095 S		–	0.20	0.21	
	BAT 15-115 S		–	0.16	0.18	
Forward voltage		V_F				V
I_F = 1 mA	BAT 15-025 S		–	0.26	–	
	BAT 15-055 S		–	0.28	–	
	BAT 15-095 S		–	0.30	–	
	BAT 15-115 S		–	0.31	–	
I_F = 10 mA	BAT 15-025 S		–	0.35	–	
	BAT 15-055 S		–	0.39	–	
	BAT 15-095 S		–	0.44	–	
	BAT 15-115 S		–	0.45	–	
Single sideband noise figure		F_{SSB}				dB
F_{IF} = 1.5 dB, P_{LO} = 0 dBm, f_{IF} = 10.7 MHz						
f = 3.0 GHz	BAT 15-025 S		–	6.0	–	
f = 6.0 GHz	BAT 15-055 S		–	6.5	–	
f = 9.3 GHz	BAT 15-095 S		–	6.5	–	
f = 16 GHz	BAT 15-115 S		–	7.0	–	
Differential forward resistance		r_f				Ω
I_F = 10 / 50 mA	BAT 15-025 S		–	3.5	–	
	BAT 15-055 S		–	4.0	–	
	BAT 15-095 S		–	7.0	–	
	BAT 15-115 S		–	10.0	–	

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